

International
IOR Rectifier

10MQ040N

SCHOTTKY RECTIFIER

2.1 Amp

$$I_{F(AV)} = 2.1\text{Amp}$$

$$V_R = 40\text{V}$$

Major Ratings and Characteristics

Characteristics	Value	Units
I_F DC	2.1	A
V_{RRM}	40	V
I_{FSM} @tp = 5 μ s sine	120	A
V_F @ 1.5Apk, $T_J=125^\circ\text{C}$	0.56	V
T_J range	- 55 to 150	$^\circ\text{C}$

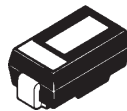
Description/ Features

The 10MQ040N surface mount Schottky rectifier has been designed for applications requiring low forward drop and very small foot prints on PC boards. Typical applications are in disk drives, switching power supplies, converters, free-wheeling diodes, battery charging, and reverse battery protection.

- Small foot print, surface mountable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability

Case Styles

10MQ040N



SMA



Voltage Ratings

Part number	10MQ040N
V_R Max. DC Reverse Voltage (V)	40
V_{RWM} Max. Working Peak Reverse Voltage (V)	

Absolute Maximum Ratings

Parameters	10MQ	Units	Conditions
$I_{F(AV)}$ Max. Average Forward Current * See Fig. 4	1.5	A	50% duty cycle @ $T_L = 123^\circ\text{C}$, rectangular wave form. On PC board 9mm^2 island ($.013\text{mm}$ thick copper pad area)
I_{FSM} Max. Peak One Cycle Non-Repetitive Surge Current * See Fig. 6	120	A	Following any rated load condition and with rated V_{RWM} applied
	30		
E_{AS} Non-Repetitive Avalanche Energy	3.0	mJ	$T_J = 25^\circ\text{C}$, $I_{AS} = 1\text{A}$, $L = 6\text{mH}$
I_{AR} Repetitive Avalanche Current	1.0	A	

Electrical Specifications

Parameters	10MQ	Units	Conditions
V_{FM} Max. Forward Voltage Drop (1) * See Fig. 1	0.54	V	@ 1A
	0.62	V	@ 1.5A
	0.49	V	@ 1A
	0.56	V	@ 1.5A
I_{RM} Max. Reverse Leakage Current (1) * See Fig. 2	0.5	mA	$T_J = 25^\circ\text{C}$
	26	mA	$T_J = 125^\circ\text{C}$
$V_{F(TO)}$ Threshold Voltage	0.36	V	$T_J = T_J \text{ max.}$
r_f Forward Slope Resistance	104	$\text{m}\Omega$	
C_T Typical Junction Capacitance	38	pF	$V_R = 10V_{DC}$, $T_J = 25^\circ\text{C}$, test signal = 1Mhz
L_S Typical Series Inductance	2.0	nH	Measured lead to lead 5mm from package body
dv/dt Max. Voltage Rate of Change (Rated V_R)	10000	V/ μs	

(1) Pulse Width < 300 μs , Duty Cycle < 2%

Thermal-Mechanical Specifications

Parameters	10MQ	Units	Conditions
T_J Max. Junction Temperature Range (*)	-55 to 150	$^\circ\text{C}$	
T_{stg} Max. Storage Temperature Range	-55 to 150	$^\circ\text{C}$	
R_{thJA} Max. Thermal Resistance Junction to Ambient	80	$^\circ\text{C}/\text{W}$	DC operation
wt Approximate Weight	0.07(0.002)	g (oz.)	
Case Style	SMA		Similar D-64
Device Marking	IR1F		

(*) $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink